
2SK435

Silicon N-Channel Junction FET

HITACHI

Application

Low frequency / High frequency amplifier

Outline

TO-92 (2)



- 1. Drain
- 2. Source
- 3. Gate

2SK435

Absolute Maximum Ratings (Ta = 25°C)

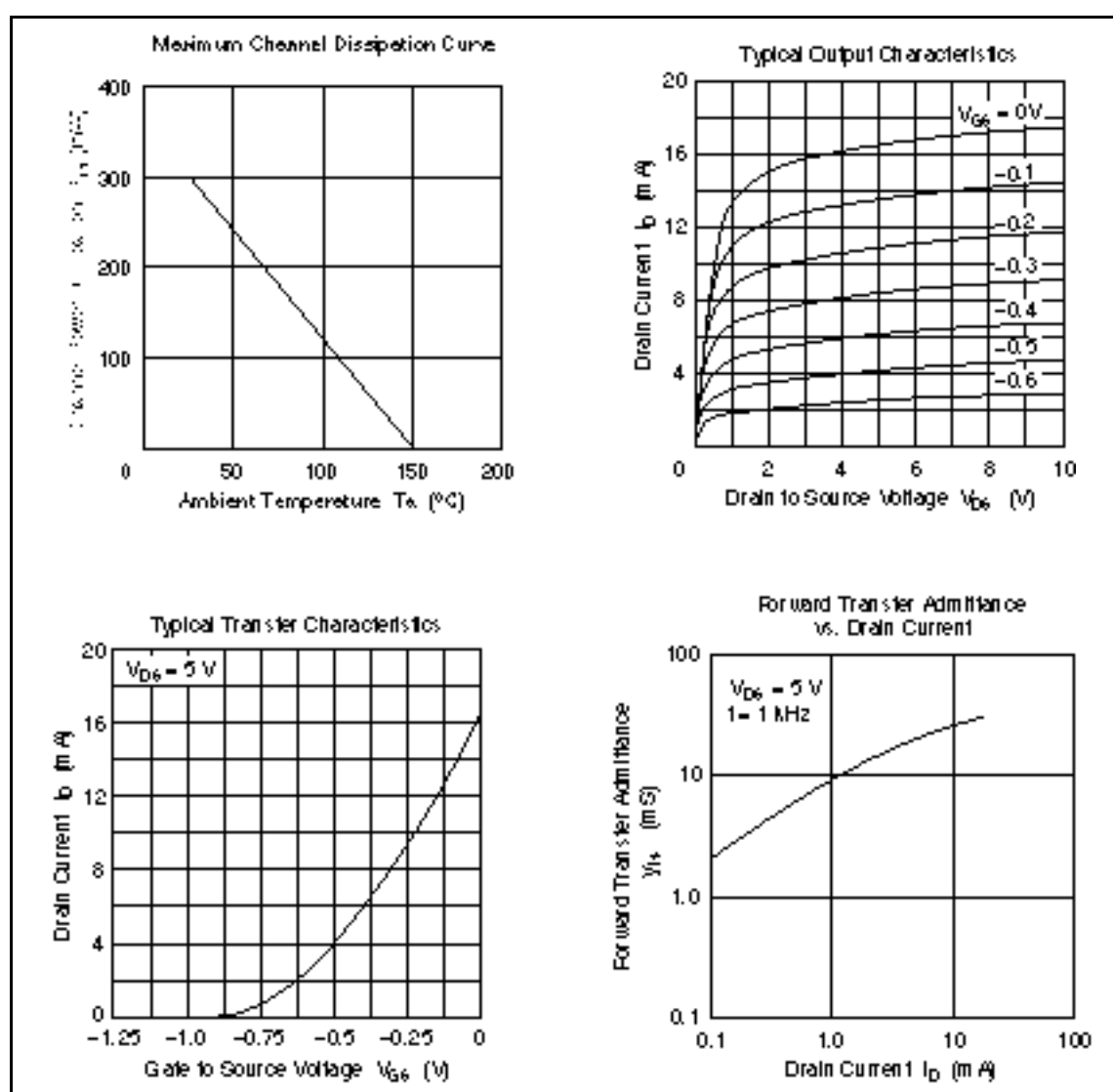
Item	Symbol	Ratings	Unit
Drain to source voltage	V_{DS}	22	V
Gate to source voltage	V_{GSO}	-22	V
Drain current	I_D	100	mA
Gate current	I_G	10	mA
Channel power dissipation	Pch	300	mW
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

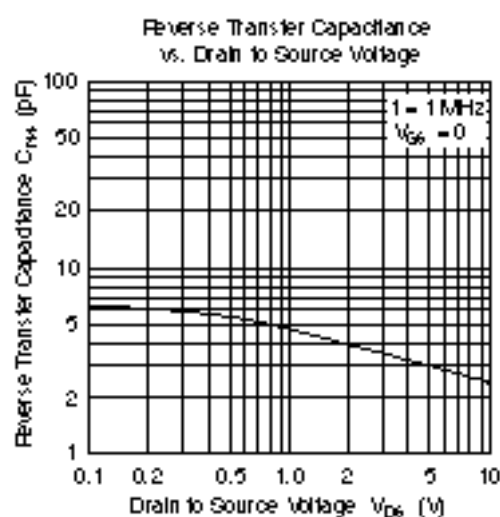
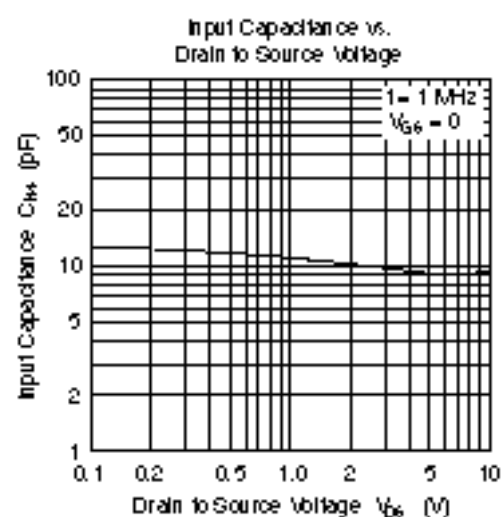
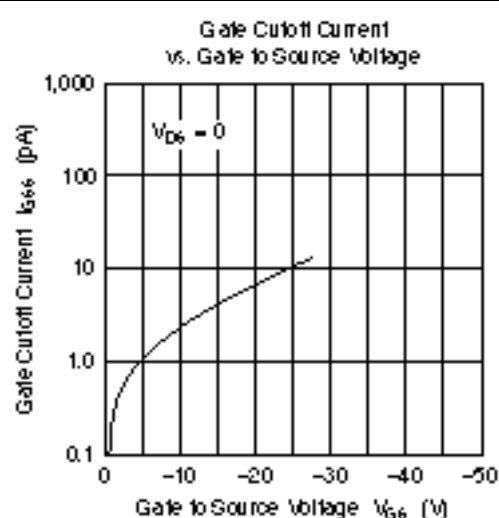
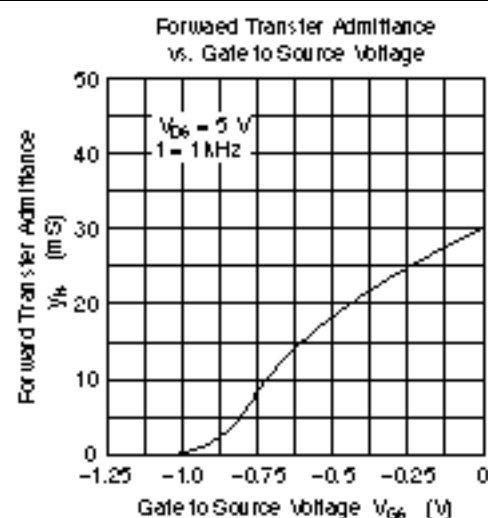
Electrical Characteristics (Ta = 25°C)

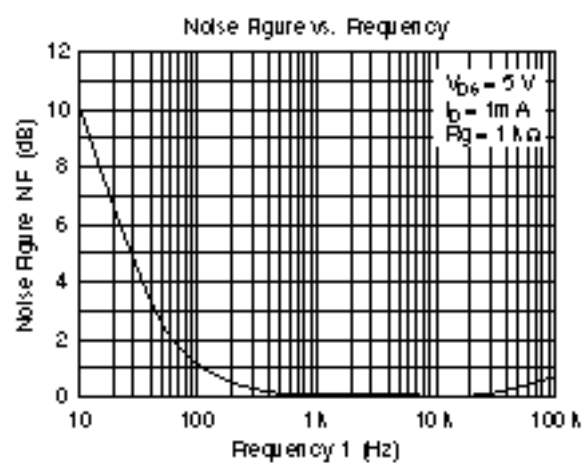
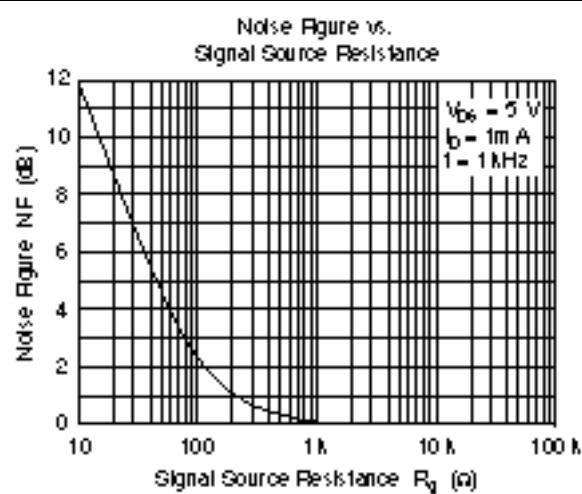
Item	Symbol	Min	Typ	Max	Unit	Test conditions
Gate to source breakdown voltage	$V_{(BR)GSS}$	-22	—	—	V	$I_G = -10 \mu A$, $V_{DS} = 0$
Gate cutoff current	I_{GSS}	—	—	-10	nA	$V_{GS} = -15 V$, $V_{DS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	—	—	-2.5	V	$V_{DS} = 5 V$, $I_D = 10 \mu A$
Drain current	I_{DSS}^{*1}	6	—	40	mA	$V_{DS} = 5 V$, $V_{GS} = 0$, Pulse test
Forward transfer admittance	$ y_{fs} $	20	—	—	mS	$V_{DS} = 5 V$, $I_D = 10 mA$, $f = 1 kHz$
Input capacitance	Ciss	—	9.0	11.0	pF	$V_{DS} = 5 V$, $V_{GS} = 0$, $f = 1 MHz$
Reverse transfer capacitance	Crss	—	2.8	4.0	pF	$V_{DS} = 5 V$, $V_{GS} = 0$, $f = 1 MHz$
Noise figure	NF	—	0.5	3.0	dB	$V_{DS} = 5 V$, $I_D = 1 mA$, $f = 1 kHz$, $R_g = 1 kW$

Note: 1. The 2SK435 is grouped by I_{DSS} as follows.

Grade	B	C	D	E
I_{DSS}	6 to 14	12 to 22	18 to 30	26 to 40







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